

Identification

DRF2666E/16GB 2Gx72
16GB 2Rx8 PC4-2666V-E-19

Performance Range

Clock / Module Speed / CL-t_{RCD}-t_{RP}
1333MHz / PC4-2666 / 19-19-19
1200 MHz / PC4-2400 / 17-17-17
1067MHz / PC4-2133 / 15-15-15
933 Hz / PC4-1866 / 13-13-13
800 Hz / PC4-1600 / 11-11-11



Features

288-pin JEDEC-compliant DIMM, 133.35 mm wide by 31.25 mm high
Operating Voltage: VDD/VDDQ = 1.2V (1.14V to 1.26V)
VPP = 2.5V (2.375V to 2.75V)
VDDSPD = 2.25V to 2.75V
I/O Type: 1.2 V signaling
On-board I²C temperature sensor with integrated Serial Presence-Detect (SPD) EEPROM
Data Transfer Rate: 21.3 Gigabytes/sec
Data Bursts: 8 and burst chop 4 mode
ZQ Calibration for Output Driver and On-Die Termination (ODT)
Programmable ODT / Dynamic ODT during Writes
Programmable CAS Latency: 10, 11, 12, 13, 14, 15, 16, 17, 18, and 19
Bi-directional Differential Data Strobe signals
Per DRAM Addressability is supported
Write CRC is supported at all speed grades
DBI (Data Bus Inversion) is supported(x8 only)
CA parity (Command/Address Parity) mode is supported
Supports ECC error correction and detection
16 internal banks
SDRAM Addressing (Row/Col/BG/BA): 16/10/2/2
Fully RoHS Compliant

Description

DRF2666E/16GB is an Unbuffered 2Gx72 memory module, which conforms to JEDEC's DDR4-2666, PC4-2666 standard. The assembly is Dual-Rank. Each rank is comprised of nine 1Gx8 DDR4-2666 SDRAMs.

One EEPROM is used for Serial Presence Detect.

Both output driver strength and input termination impedance are programmable to maintain signal integrity on the I/O signals in a Fly-by topology.

Notes

Tolerances on all dimensions except where otherwise indicated are ± 0.13 (.005).
All dimensions are expressed in millimeters [inches]

